

**/ Descriptions**

SOT-23          NPN                          Silicon NPN transistor in a SOT-23 Plastic Package.

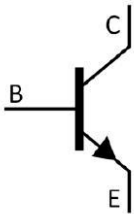
**/ Features**

BR8550MQ                  AEC-Q101  
Complementary pair with BR8550MQ, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

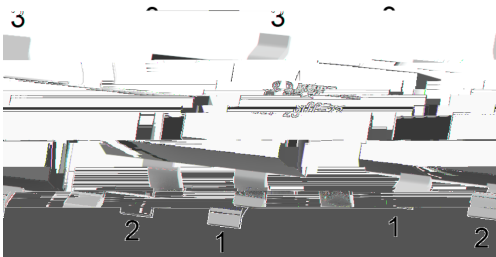
**/ Applications**

Power amplifier applications, Meet the stringent requirements of automotive applications.

**/ Equivalent Circuit**



**/ Pinning**



PIN1 Base          PIN 2 Emitter          PIN 3 Collector

**/ h<sub>FE</sub> Classifications & Marking**

h<sub>FE</sub> Classifications  
Symbol 3

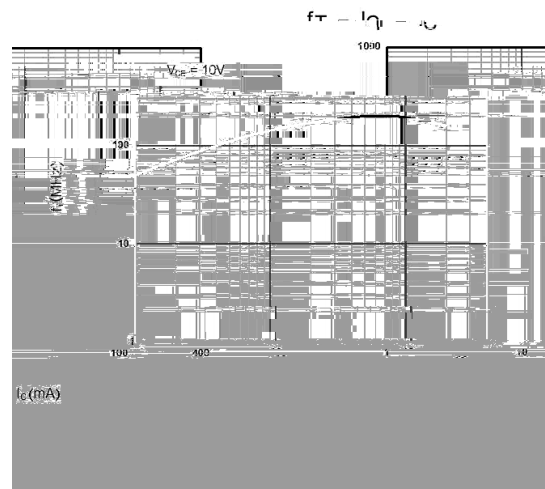
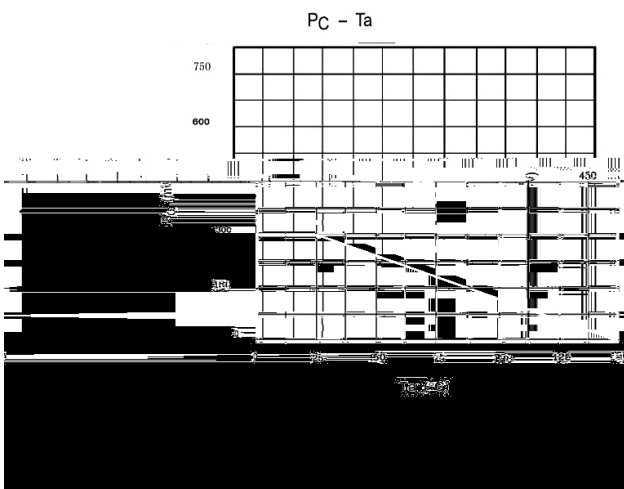
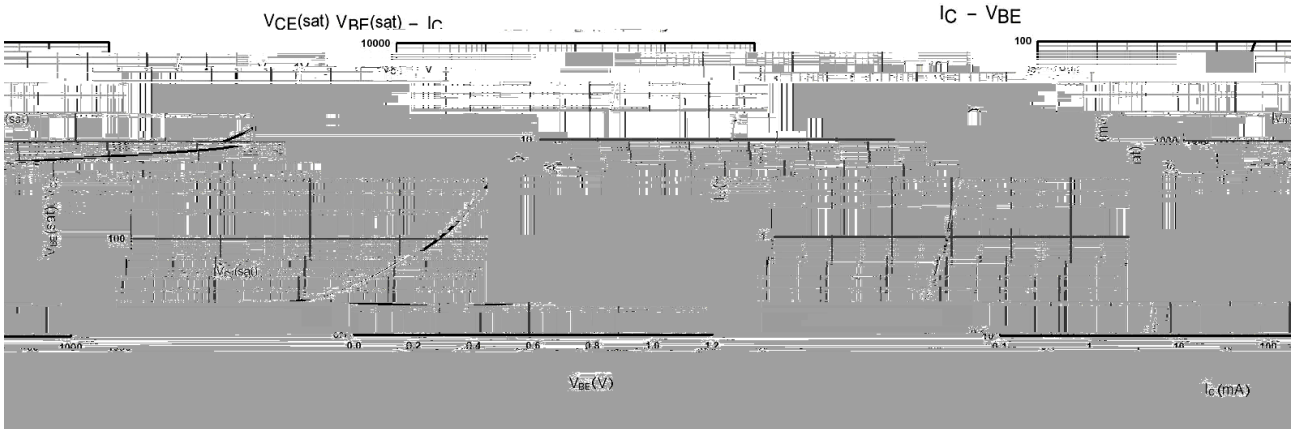
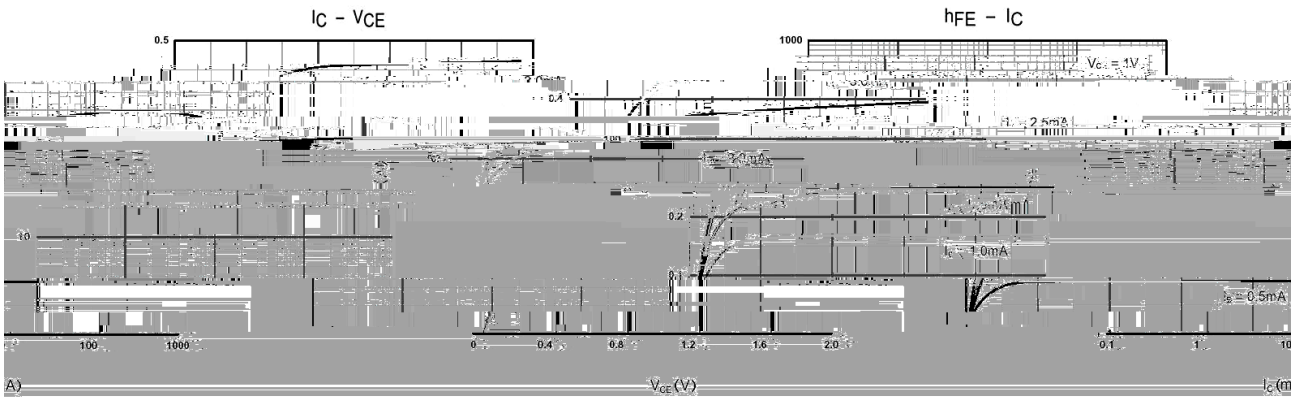
**/ Absolute Maximum Ratings(Ta=25 )**

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V <sub>CBO</sub>	40	V
Collector to Emitter Voltage	V <sub>CEO</sub>	25	V
Emitter to Base Voltage	V <sub>EBO</sub>	6	V
Collector Current - Continuous	I <sub>C</sub>	1.5	A
Base Current	I <sub>B</sub>	0.5	A
Collector Power Dissipation	P <sub>C</sub>	300	mW
Junction Temperature	T <sub>j</sub>	150	
Storage Temperature Range	T <sub>stg</sub>	-55 150	

**/ Electrical Characteristics(Ta=25 )**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V <sub>CBO</sub>	I <sub>C</sub> =0.1mA I <sub>E</sub> =0	40			V
Collector to Emitter Breakdown Voltage	V <sub>CEO</sub>	I <sub>C</sub> =2.0mA I <sub>B</sub> =0	25			V
Emitter to Base Breakdown Voltage	V <sub>EBO</sub>	I <sub>C</sub> =0.1mA I <sub>C</sub> =0	6.0			V
Collector Cut-Off Current	I <sub>CBO</sub>	V <sub>CB</sub> =35V I <sub>E</sub> =0			0.1	μA
Emitter Cut-Off Current	I <sub>EBO</sub>	V <sub>EB</sub> =6.0V I <sub>C</sub> =0			0.1	μA
DC Current Gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =1.0V I <sub>C</sub> =100mA	85		300	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =1.0V I <sub>C</sub> =800mA	40			
	h <sub>FE(3)</sub>	V <sub>CE</sub> =1.0V I <sub>C</sub> =5.0mA	45			
Collector to Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =800mA I <sub>B</sub> =80mA		0.28	0.5	V
Base to Emitter Voltage	V <sub>BE</sub>	V <sub>CE</sub> =1.0V I <sub>C</sub> =10mA		0.66	1.0	V
Base to Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =800mA I <sub>B</sub> =80mA		0.98	1.2	V
Transition Frequency	f <sub>T</sub>	I <sub>C</sub> =50mA V <sub>CE</sub> =10V	100	190		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V I <sub>E</sub> =0 f=1.0MHz		9.0		pF

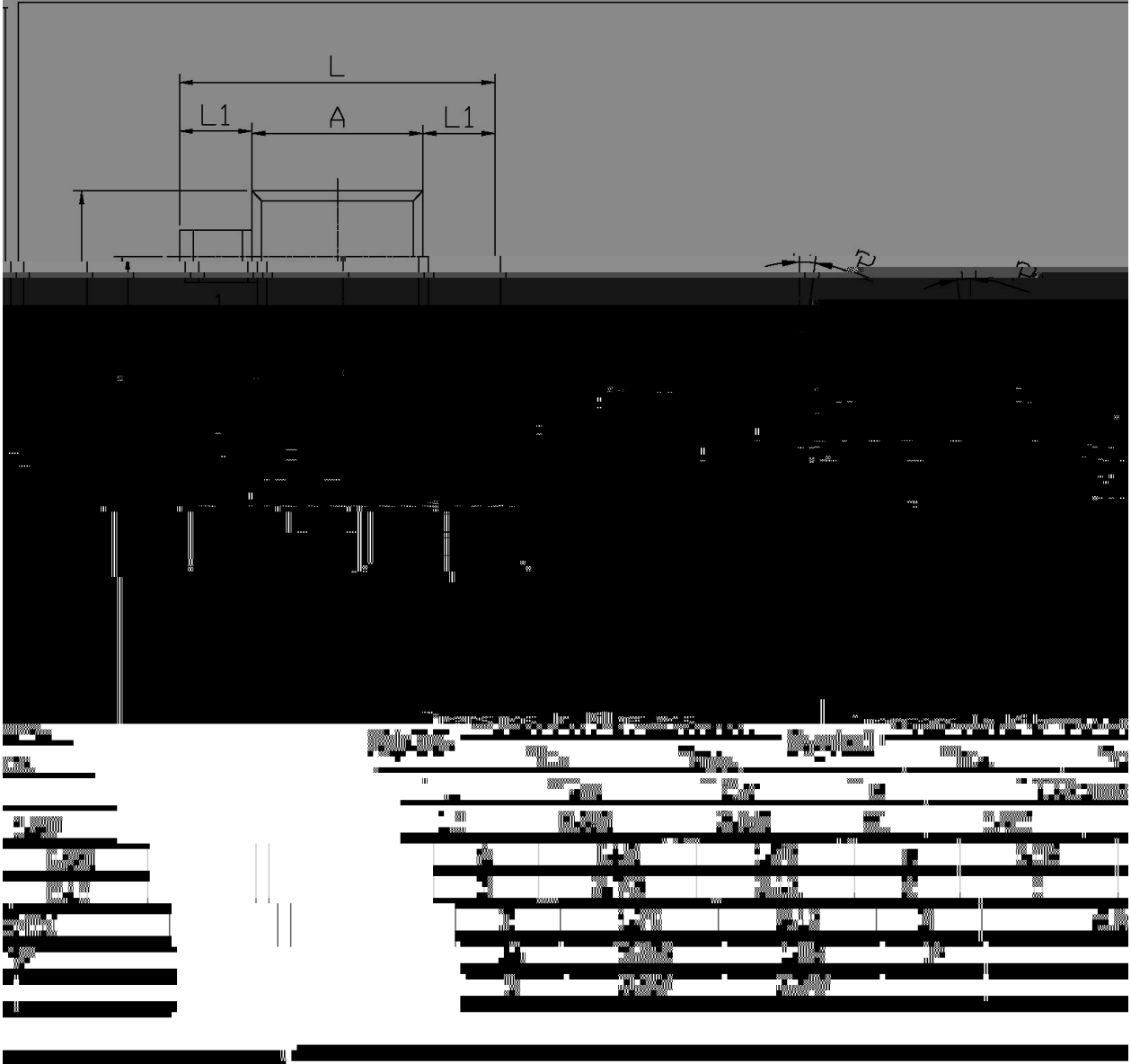
/ Electrical Characteristic Curve



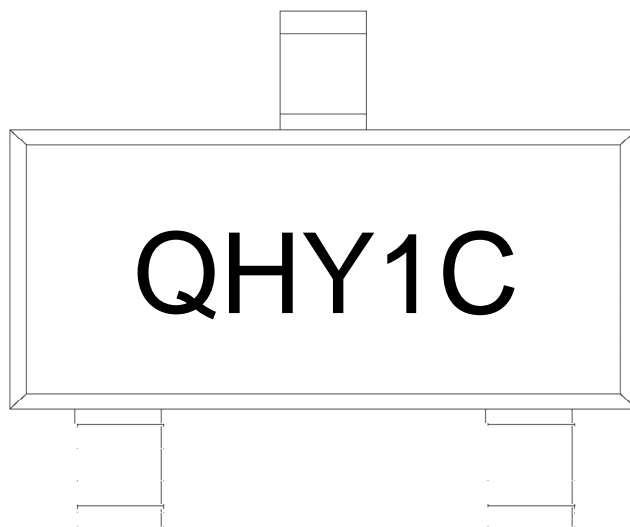
/ Package Dimensions

SOT-23

单位: mm



/ Marking Instructions



Q

H

Y1

C

$h_{FE}$

Note:

Q: Automobile halogen-free product Code

H: Company Code.

Y1: Product Type .

C:  $h_{FE}$  Classifications Symbol Code.

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)


Note:

1            150   200            60